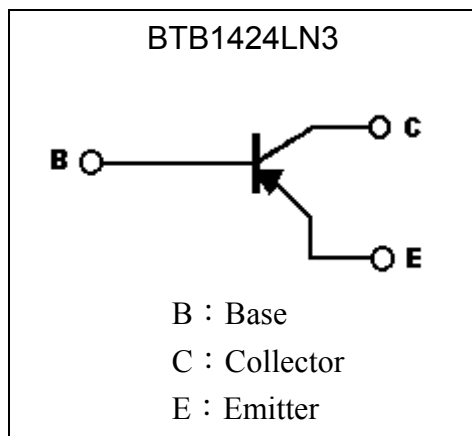
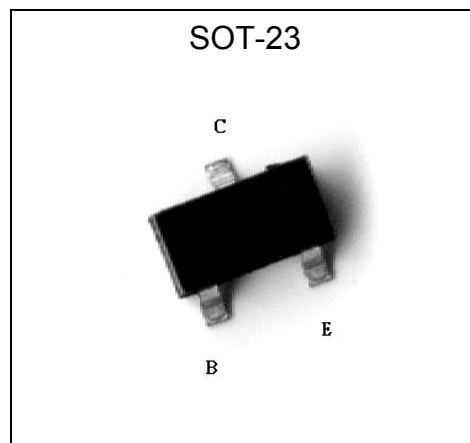


Low $V_{CE(sat)}$ PNP Epitaxial Planar Transistor

BTB1424LN3

Features

- Low $V_{CE(sat)}$, typically -0.3 V at $I_C / I_B = -2A / -0.2A$
- Excellent current gain characteristics
- Complementary to BTB2150LN3

Symbol

Outline

Absolute Maximum Ratings ($T_a=25^{\circ}\text{C}$)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current (DC)	I_C	-3	A
Collector Current (Pulse)	I_{CP}	-7 (Note)	A
Power Dissipation	P_d	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

 Note : Single Pulse $P_w \leq 350\mu\text{s}$, Duty $\leq 2\%$.



Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	-40	-	-	V	I _C =-50μA, I _E =0
BV _{CEO}	-30	-	-	V	I _C =-1mA, I _B =0
BV _{EBO}	-5	-	-	V	I _E =-50μA, I _C =0
I _{CBO}	-	-	-1	μA	V _{CB} =-30V, I _E =0
I _{EBO}	-	-	-1	μA	V _{EB} =-3V, I _C =0
*V _{CE(sat)}	-	-0.3	-0.5	V	I _C =-2A, I _B =-0.2A
*V _{BE(sat)}	-	-1	-2	V	I _C =-2A, I _B =-0.2A
*h _{FE1}	52	-	-	-	V _{CE} =-2V, I _C =-20mA
*h _{FE2}	100	-	500	-	V _{CE} =-2V, I _C =-1A
f _T	-	80	-	MHz	V _{CE} =-5V, I _C =-0.1A, f=100MHz
C _{ob}	-	55	-	pF	V _{CB} =-10V, f=1MHz

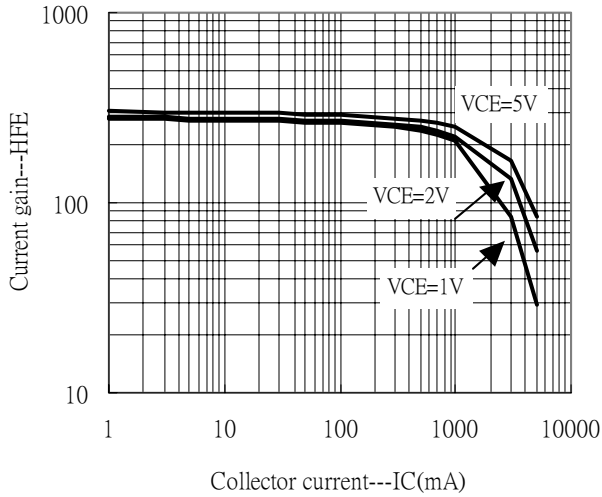
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of hFE2

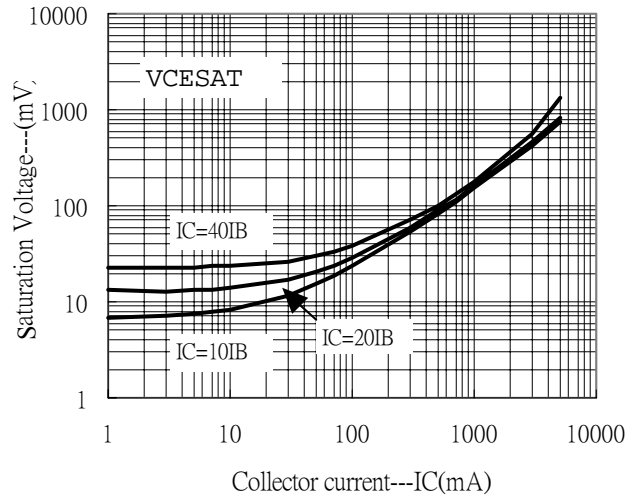
Rank	Q	P	E
Range	100~200	160~320	250~500

Characteristic Curves

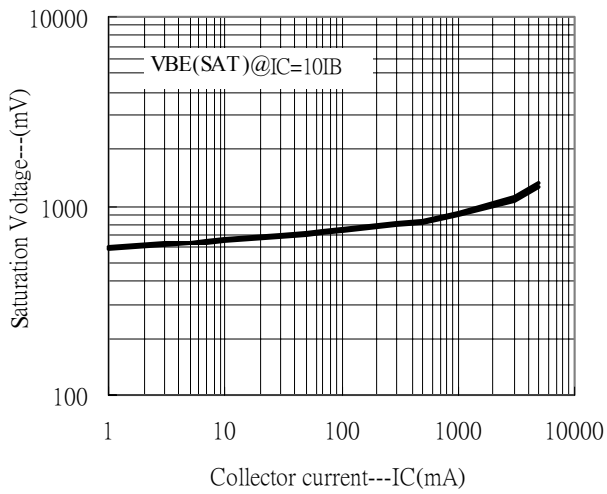
Current gain vs Collector current



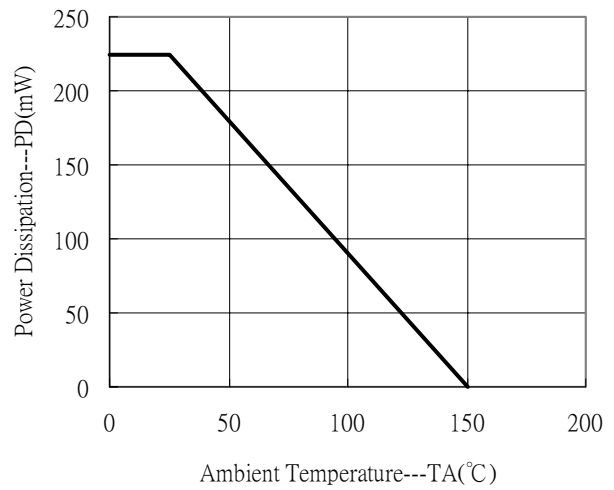
Saturation Voltage vs Collector current



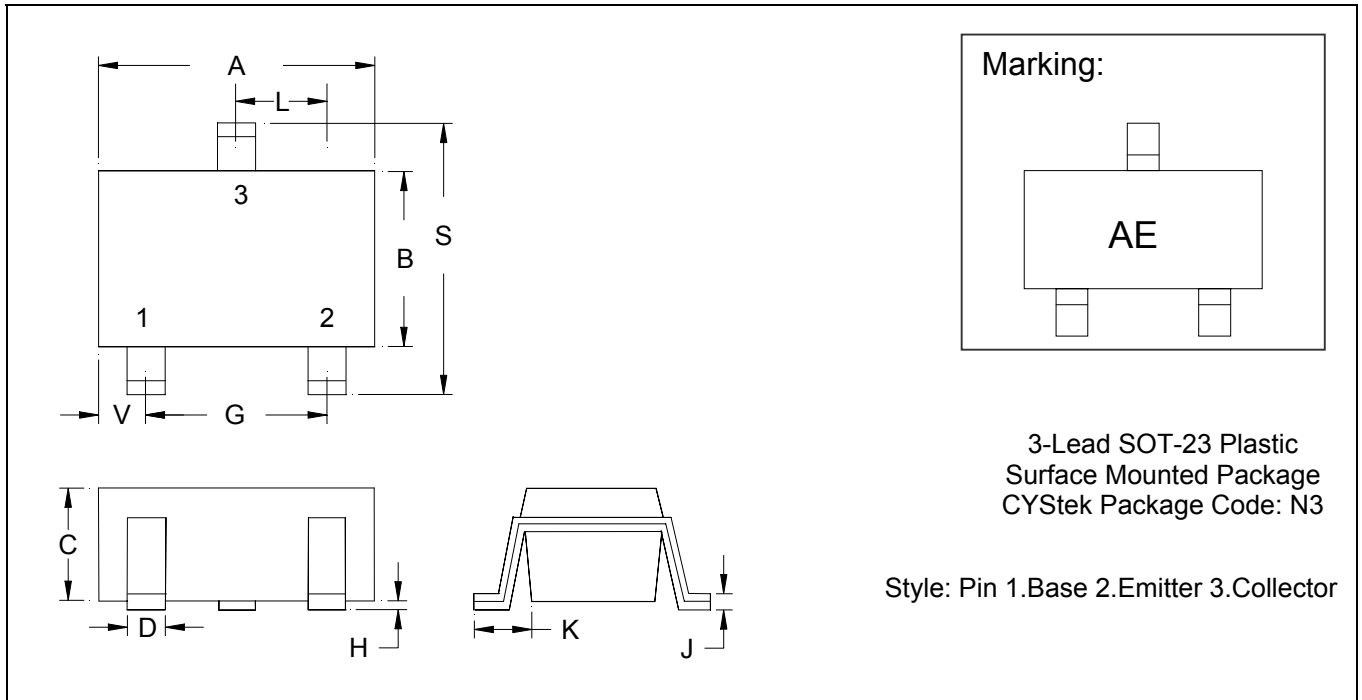
Saturation Voltage vs Collector current



Power Derating Curve



SOT-23 Dimension



*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1102	0.1204	2.80	3.04	J	0.0034	0.0070	0.085	0.177
B	0.0472	0.0630	1.20	1.60	K	0.0128	0.0266	0.32	0.67
C	0.0335	0.0512	0.89	1.30	L	0.0335	0.0453	0.85	1.15
D	0.0118	0.0197	0.30	0.50	S	0.0830	0.1083	2.10	2.75
G	0.0669	0.0910	1.70	2.30	V	0.0098	0.0256	0.25	0.65
H	0.0005	0.0040	0.013	0.10					

- Notes:**
- 1.Controlling dimension: millimeters.
 - 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 - 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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